Abstracts

A bias and temperature dependent noise model of heterojunction bipolar transistors

R.A. Pucel, T. Daniel, A. Kain and R. Tayrani. "A bias and temperature dependent noise model of heterojunction bipolar transistors." 1998 MTT-S International Microwave Symposium Digest 98.1 (1998 Vol. I [MWSYM]): 141-144.

A bias and temperature dependent HBT noise model based on an extension of the van der Ziel noise theory is presented. An extrapolation technique is applied to the noise model that is valid for the entire bias and temperature operating range of the HBT given experimental data for a single reference condition.

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